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Karen Cinq-Mars 9/10/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE	
In Re Application of: Edward P. Barth et al.	September 10, 2003
	Examiner: Christy L. Novacek
Based on Serial No. 09/467,207 Filing Date: 12/20/1999	Group Art Unit: 2822
Title: Dual Damascene Interconnect Structure Using Low Stress Flourosilicate Insulator with Copper Conductors	IBM Corporation 2070 Route 52 Hopewell Junction New York 12533

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313

Prior to the examination of the application please amend the claims as follows:

20. (Currently Amended) A metallization insulating structure, comprising:

A [substantially planar substrate, the substrate having underlying] substrate having
metal structures therein;

A first layer, the first layer a substantially fluorine free insulating layer formed on the substrate, having a height, h_i ;

A second layer, the second layer a fluorine containing insulating layer formed directly on the first layer, having a height h_f ;

A metal structure of at least height $h_i + h_f$ formed in the first and second layer, the metal structure extending to the substantially planar substrate.

21. (Currently amended) The metallization insulating structure of claim 20 further comprising a capping layer on the substrate, underlying the first layer.

22. (Currently amended) The metallization insulating structure according to claim 20 wherein the fluorine containing insulating layer comprises a material selected from the group consisting of fluorinated silicon oxide, fluorinated amorphous carbon, fluorinated diamondlike carbon and fluorinated organic polymers.

23. (Currently amended) The metallization insulating structure according to claim 20 wherein the substantially free insulating layer comprises undoped silicon glass.

24. (Previously presented) The metallization insulating structure according to claim 21 wherein the capping layer comprises a material selected from the group consisting of silicon nitride, silicon carbide and hydrogenated silicon carbide, or combinations thereof.